

ABSTRACT OF THE DISCLOSURE

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A bipolar transistor with high performance and high reliability, which is obtained by enhancing a withstand voltage between an emitter and a base; and a method of fabricating the same. The bipolar transistor includes a first impurity diffusion layer in a semiconducting substrate; a first conductive film connected to the first diffusion layer; an opening disposed in the first conductive layer; a second impurity diffusion layer formed in a portion, exposed from the opening portion, of the semiconducting substrate and connected to the first impurity diffusion layer; a third impurity diffusion layer formed so as to contain the second diffusion layer; side walls formed on the side walls of the opening; and a fourth impurity diffusion layer in the third impurity diffusion layer in the opening surrounded by the side walls.

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